



THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of
SOWLATI et al.

Atty. Docket US000099

9/B

Application No. 09/545,785

Group Art Unit: 2811

FJONES
1-15-02

Filed: April 7, 2000

Examiner: O. Nadav

For: INTERDIGITATED MULTILAYER
CAPACITOR STRUCTURE FOR DEEP SUB-
MICRON CMOS

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

RECEIVED
JAN 10 2002
TC 2800 MAIL ROOM

Sir:

Preliminary to examination of the application filed
herewith, please amend the above referenced application as follows.

In the Claims:

Please cancel, add, and/or rewrite the claim(s) as
follows per 37 CFR § 1.121(c) (1).

Subt C
1. (Twice Amended) A capacitor comprising:

a first level of at least four electrically conductive
parallel lines extending in a first direction and lying in a first
plane;

at least a second level of at least four electrically
conductive parallel lines extending in the first direction and